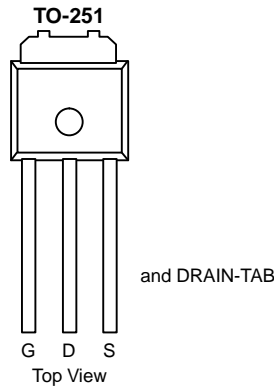




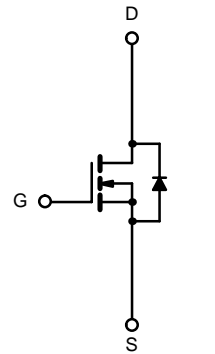
N-Channel 100-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
100	0.200 @ V _{GS} = 10 V	6.5
	0.225 @ V _{GS} = 4.5 V	6.0

175°C Rated
Maximum Junction Temperature
TrenchFET®
Power MOSFETS



Order Number:
SUU06N10-225L



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	
Continuous Drain Current (T _J = 175°C) ^b	T _C = 25°C	I _D	6.5	A
	T _C = 125°C		3.75	
Pulsed Drain Current		I _{DM}	8.0	
Continuous Source Current (Diode Conduction)		I _S	6.5	
Avalanche Current		I _{AR}	5.0	
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E _{AR}	1.25	mJ
Maximum Power Dissipation	T _C = 25°C	P _D	20 ^b	W
	T _A = 25°C		1.5 ^a	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	40	50	°C/W
	Steady State		80	100	
Junction-to-Case		R _{thJC}	6.0	7.5	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. See SOA curve for voltage derating.

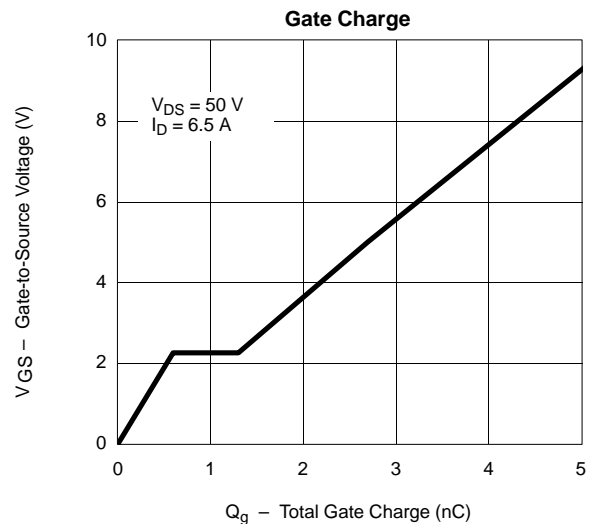
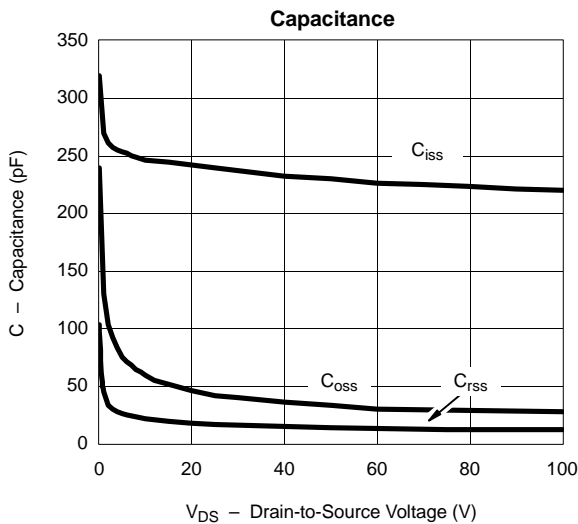
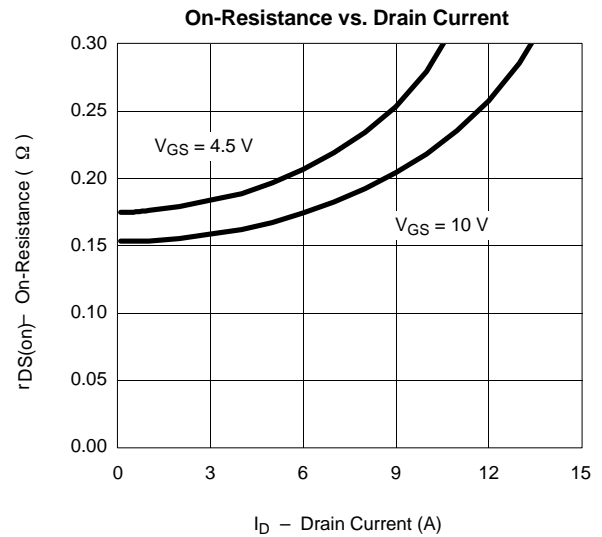
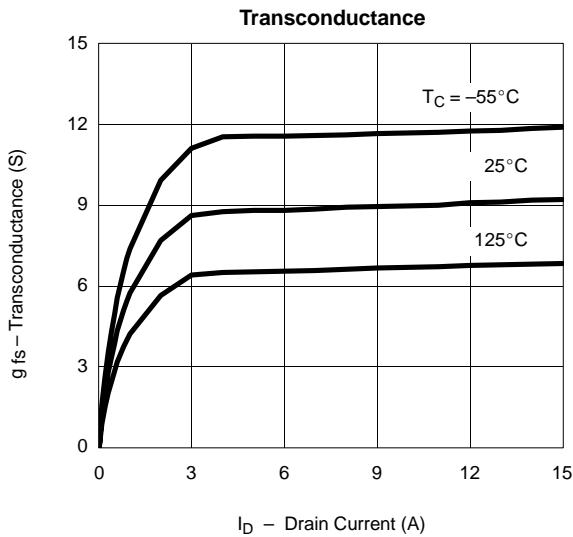
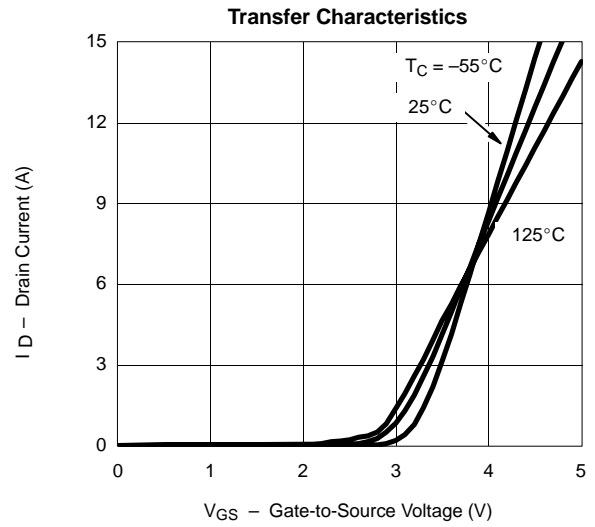
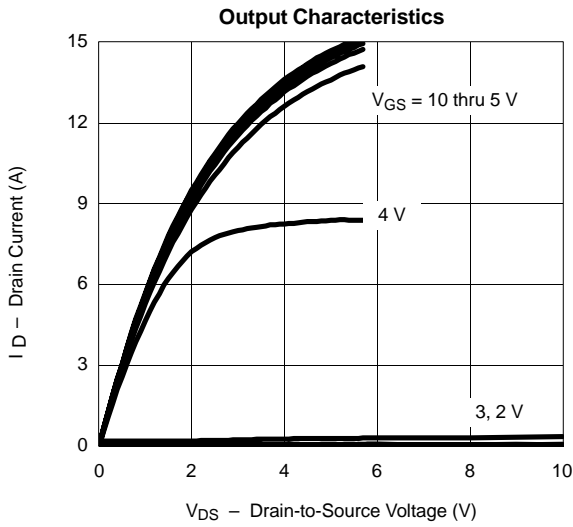
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			1	μA
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	8.0			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 3 A		0.160	0.200	Ω
		V _{GS} = 10 V, I _D = 3 A, T _J = 125 °C			0.350	
		V _{GS} = 10 V, I _D = 3 A, T _J = 175 °C			0.450	
		V _{GS} = 4.5 V, I _D = 1.0 A		0.180	0.225	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 3 A		8.5		S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, F = 1 MHz		240		pF
Output Capacitance	C _{oss}			42		
Reverse Transfer Capacitance	C _{rss}			17		
Total Gate Charge ^c	Q _g	V _{DS} = 50 V, V _{GS} = 5 V, I _D = 6.5 A		2.7	4.0	nC
Gate-Source Charge ^c	Q _{gs}			0.6		
Gate-Drain Charge ^c	Q _{gd}			0.7		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 7.5 Ω I _D = 6.5 A, V _{GEN} = 10 V, R _G = 2.5 Ω		7	11	ns
Rise Time ^c	t _r			8	12	
Turn-Off Delay Time ^c	t _{d(off)}			8	12	
Fall Time ^c	t _f			9	14	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I _{SM}				8.0	A
Diode Forward Voltage ^b	V _{SD}	I _F = 6.5 A, V _{GS} = 0 V		0.9	1.3	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 6.5 A, di/dt = 100 A/μs		35	60	ns

Notes

- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

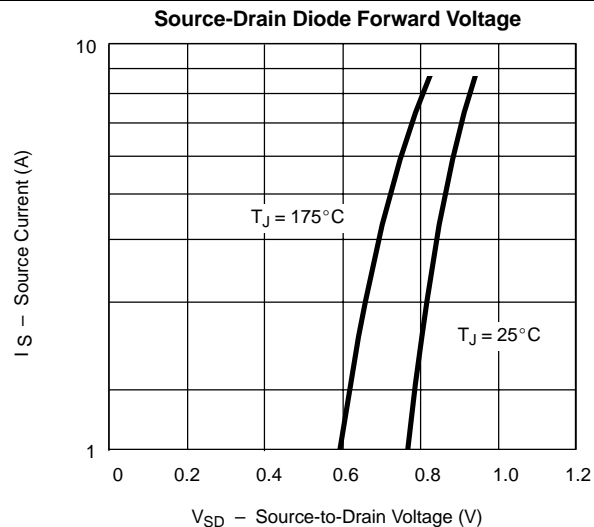
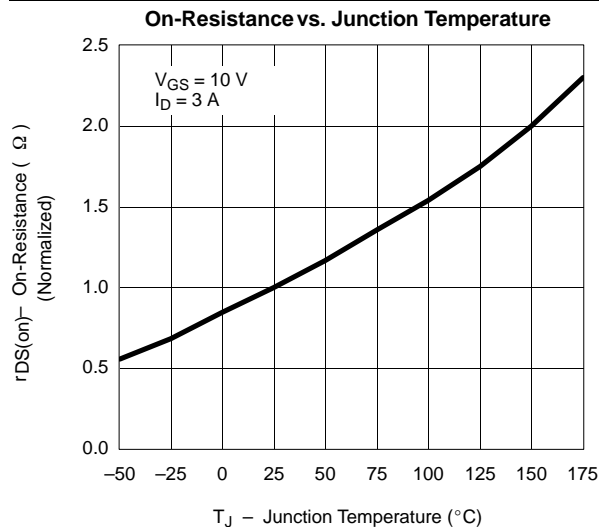


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

